

#### **Features**

-3dB Bandwidth: 550MHz

Supply Range: +1.8V to +5.5V

RON is Typically 6Ω

Fast Switching Times: ton 20ns, toff 15ns

Break-Before-Make Switching

■ Low Power Consumption (1µA Maximum)

Rail-to-Rail Input and Output Operation

Temperature Range: -40°C to +125°C

Micro Size Packages: SOT23-6

### **Application**

Wearable Devices

Battery-Operated Equipment

 Signal Gating, Chopping, Modulation or Demodulation (Modem)

Portable Computing

Cell Phones

### **Description**

The RS3SW2157 is a single-pole double-throw (SPDT) analog switch that is designed to operate from 1.8 V to 5.5 V.

The RS3SW2157 device can handle both analog and digital signals. It features high-bandwidth (550MHz) and low on-resistance ( $6\Omega$  TYP).

Applications include signal gating, chopping, modulation or demodulation (modem), and signal multiplexing for analog-to-digital and digital-to-analog conversion systems.

### **Ordering Information**

Part Number	Package	Description
RS3SW2157T	SOT23-6	2.92mm x 1.62mm

1

# **Pin Configuration**

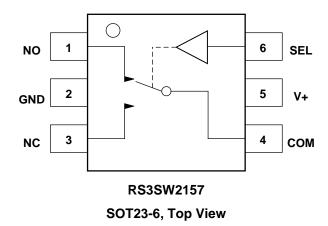


Table 1. Pin Functions: RS3SW2157

NAME	PIN	FUNCTION
NAME	SOT23-6	FUNCTION
NO	1	Normally-Open Terminal
GND	2	Ground
NC	3	Normally-Closed Terminal
COM	4	Common Terminal
V+	5	Power Supply
SEL	6	Digital Control Pin

## **Function Table**

LOGIC	NO	NC
0	OFF	ON
1	ON	OFF

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### **Absolute Maximum Ratings**

Over operating free-air temperature range (unless otherwise noted) (1)

SYMBOL	PARAMETER	MIN	MAX	UNIT	
V+	Supply Voltage		-0.3	6.0	
Vin	Input Voltage <sup>(2)</sup>		-0.3	6.0	V
	Analog, Digital Voltage Range		-0.3	(V <sub>+</sub> )+0.3	
	Continuous Current NO, NC, or COM		-100	+100	mA
Іреак	Peak Current NO, NC, or COM		-150	+150	
θЈА	Package thermal impedance (3)	SOT23-6		235	°C/W
TJ	Junction Temperature (4)	-40	150	°C	
T <sub>stg</sub>	Storage temperature		-65	+150	

<sup>(1)</sup> Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not implied.

## **ESD Ratings**

The following ESD information is provided for handling of ESD-sensitive devices in an ESD protected area only.

SYMBOL	PARAMETER		VALUE	UNIT
	Human-Body Model (HBM)	±4000	٧	
V (ESD)	V <sub>(ESD)</sub> Electrostatic discharge	Charged-Device Model (CDM)	±1000	٧

## **Recommended Operating Conditions**

Over operating free-air temperature range (unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNIT
Vcc	Supply Voltage	1.8	5.5	V
TA	Operating temperature	-40	+125	°C

<sup>(2)</sup> Input terminals are diode-clamped to the power-supply rails. Input signals that can swing more than 0.3V beyond the supply rails should be current-limited to 10mA or less.

<sup>(3)</sup> The package thermal impedance is calculated in accordance with JESD-51.

<sup>(4)</sup> The maximum power dissipation is a function of  $T_{J(MAX)}$ ,  $R_{\theta JA}$ , and  $T_A$ . The maximum allowable power dissipation at any ambient temperature is  $P_D = (T_{J(MAX)} - T_A) / R_{\theta JA}$ . All numbers apply for packages soldered directly onto a PCB.



#### **Electrical Characteristics**

VDD= +1.8V to +5.5V, GND=0V, TA=-40°C to +125°C. Typical values are at VDD=+3.3V, TA=+25°C, unless otherwise noted.

PARAMETER	SYMBOL	CONDITIONS	T <sub>A</sub>	MIN <sup>(2)</sup>	<b>TYP</b> (3)	MAX <sup>(2)</sup>	UNIT
Analog Switch							
Analog Signal Range	Vno, Vnc Vcom		-40°C to +125°C	0		V+	V
On-Resistance	Ron	VDD = 3.0V, $VNC$ or $VNO = 0V$ to $0.4V$ ,	+25°C		6	10	Ω
On-Resistance	KON	I <sub>СОМ</sub> = 8mA, See Figure 1	-40°C to +125°C			10.5	Ω
On-Resistance Match	ΔRon	VDD = 3.0V, $VNC$ or $VNO = 0V$ to $0.4V$ ,	+25°C		0.15	0.6	Ω
Between Channels	ΔΚΟΝ	I <sub>COM</sub> = 8mA, See Figure 1	-40°C to +125°C			1.6	Ω
On-Resistance Flatness	RFLAT(ON)	VDD = 3.0V, VNC or VNO = 0V to 1V, ICOM = 8mA, See Figure 1	+25°C		5	7	Ω
On-Resistance Flatness			-40°C to +125°C			8	Ω
Source Off Leakage Current	Inc(off),Ino(off)	VDD = 3.6V, VCOM = 0.3V or 3.6V, VNC or VNO = 0V or 3.6 V	-40°C to +125°C			1	μΑ
Channel On Leakage Current	Inc(on), Ino(on),	V <sub>DD</sub> = 3.6V, V <sub>COM</sub> = 0.3V or 3.6V, V <sub>NC</sub> or V <sub>NO</sub> = 0V or 3.6 V or floating	-40°C to +125°C			1	μΑ
Digital Control Inputs (1)	Digital Control Inputs (1)						
Input High Voltage	VIH		-40°C to +125°C	1.6			V
Input Low Voltage	VıL		-40°C to +125°C			0.5	V
Input Leakage Current	I <sub>IN</sub>	VDD = 3.0V, VSEL = 0V or VDD	-40°C to +125°C			1	μΑ

<sup>(1)</sup> All unused digital inputs of the device must be held at  $V_{IO}$  or GND to ensure proper device operation.

<sup>(2)</sup> Limits are 100% production tested at 25°C. Limits over the operating temperature range are ensured through correlations using statistical quality control (SQC) method.

<sup>(3)</sup> Typical values represent the most likely parametric norm as determined at the time of characterization. Actual typical values may vary over time and will also depend on the application and configuration.



### **AC Electrical characteristics**

VDD= +1.8V to +5.5V, TA=-40°C to +125°C. Typical values are at VDD=+3.3V, TA=+25°C, unless otherwise noted.

PARAMETER	SYMBOL	CONDITIONS	T <sub>A</sub>	MIN	TYP	MAX	UNIT
Dynamic Characteristics.					'		
Turn-On Time	ton	$V_{IS} = 0.8V, R_{L} = 50\Omega, C_{L} = 10pF,$	+25°C		20		ns
Turn-Off Time	toff	See Figure 2	+25°C		15		ns
Break-Before-Make Time		$V_{IS} = 0.8V, R_{L} = 50\Omega, C_{L} = 10pF,$	.25%		4		
Delay	<b>t</b> BBM	See Figure 3	+25°C		0.35		ns
Propagation Delay	<b>t</b> PD	RL = $50\Omega$ , CL = $10pF$	+25°C		0.35		ns
Off Isolation	O <sub>ISO</sub>	Signal = 0dBm,R <sub>L</sub> =50Ω, Switch OFF, f =250MHz,See Figure 4	+25°C		-35		dB
-3dB Bandwidth	BW	Signal = 0dBm,Switch ON, $R_L$ = $50\Omega$ , $C_L$ = 5pF, See Figure 5	+25°C		550		MHz
Charge Injection Select Input to Common I/O	Q	VG = GND, CL = 1.0nF, RG = $0\Omega$ , Q = CL x VOUT, See Figure 6	+25°C		11		рC
NC, NO, COM ON Capacitance	Con		+25°C		7		pF
Power Requirements.							
Power Supply Range	V+		-40°C to +125°C	1.8		5.5	V
Power Supply Current	I <sub>+</sub>	VDD = 3.0V,V <sub>SEL</sub> = 0V or VDD	-40°C to +125°C			1	μА

<sup>(1)</sup> All unused digital inputs of the device must be held at VIO or GND to ensure proper device operation.

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<sup>(2)</sup> Limits are 100% production tested at 25°C. Limits over the operating temperature range are ensured through correlations using statistical

quality control (SQC) method.

Typical values represent the most likely parametric norm as determined at the time of characterization. Actual typical values may vary over time and will also depend on the application and configuration.



### **Parameter Measurement Information**

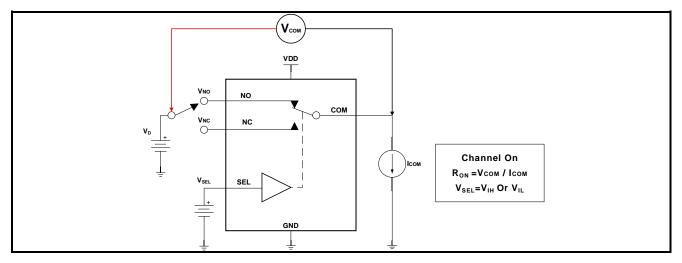


Figure 1. ON-State Resistance (Ron)

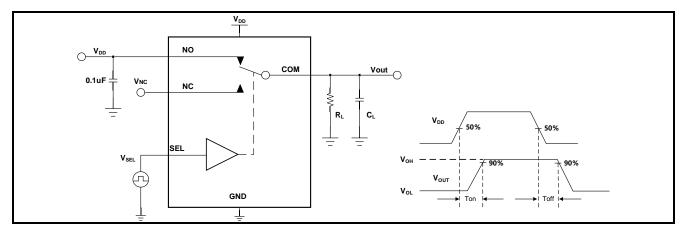
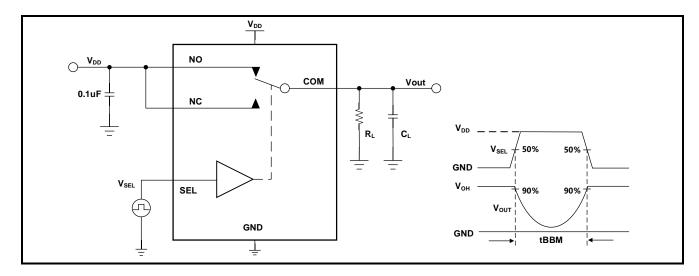


Figure 2. Turn-On (ton) and Turn-Off Time (toff)



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Figure 3、Break-Before-Make Time (t<sub>BBM</sub>)

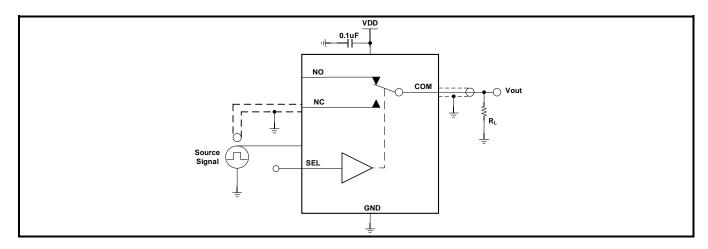


Figure 4. OFF Isolation (O<sub>ISO</sub>)

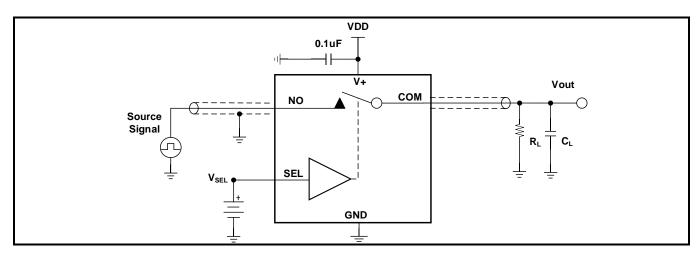


Figure 5、Bandwidth (BW)

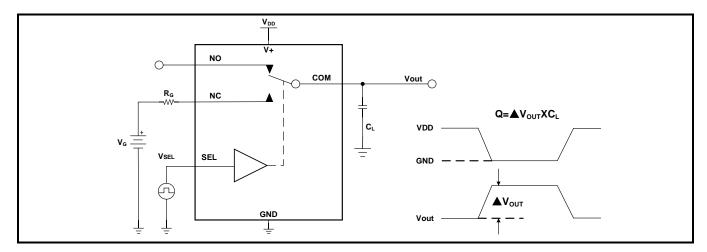
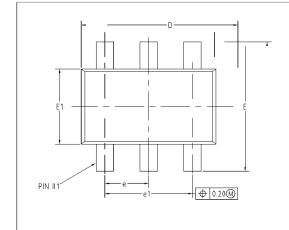


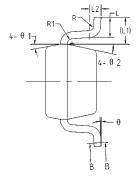
Figure 6. Charge Injection (Q)



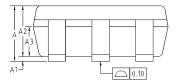
# **Package Information**

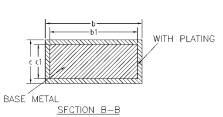
#### SOT23-6





SYMBOL	MIN	NOM	MAX
Α	_	_	1.25
A1	0	_	0.15
A2	1.00	1.10	1.20
A3	0.60	0.65	0.70
Ф	0.34	_	0.45
b1	0.34	0.38	0.41
C	0.12	_	0.20
c1	0.12	0.15	0.16
D	2.826	2.926	3.026
E	2.60	2.80	3.00
E1	1.526	1.626	1.700
е	0.90	0.95	1.00
e1	1.80	1.90	2.00
L	0.30	0.40	0.60
L1		0.59REF	
L2		0.25BSC	
R	0.05	_	0.20
R1	0.05	_	0.20
θ	0,	_	8.
θ 1	8*	10°	12 <b>°</b>
θ 2	10°	12*	14*





#### Note:

- 1.All dimensions are in mm. Angles in degrees.
- 2.Refer Jedec MO-187.
- 3. Dimensions exclude burrs, mold flash or protrusions.

SOT23-6L POD Rev:0
Raystar Microelectronics Technology Inc.



# **Revision History**

Revision	Description	DATE
V1.0	Initial Release	2025/06/30
V1.1	1.Update some parameters     2.Delete SC70-6 package     3.Modify the name of pin 6 from IN to SEL	2025/09/15